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(71) Applicant *(for all designated States except US)*: **APPLIED MATERIALS, INC.** [US/US]; 3050 Bowers Avenue, Santa Clara, California 95054 (US).

(72) Inventors; and

(75) Inventors/Applicants *(for US only)*: **LIANG, Jingmei** [CN/US]; 1256 Mountain Quail Circle, San Jose, California 95120 (US). **HONG, Sukwon** [KR/US]; 80 Descanso Drive #1407, San Jose, California 95134 (US).

(74) Agents: **BERNARD, Eugene J.** et al.; Townsend and Townsend and Crew LLP, 1400 Wewatta Street #600, Denver, Colorado 80202 (US).

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(54) Title: CURING NON-CARBON FLOWABLE CVD FILMS

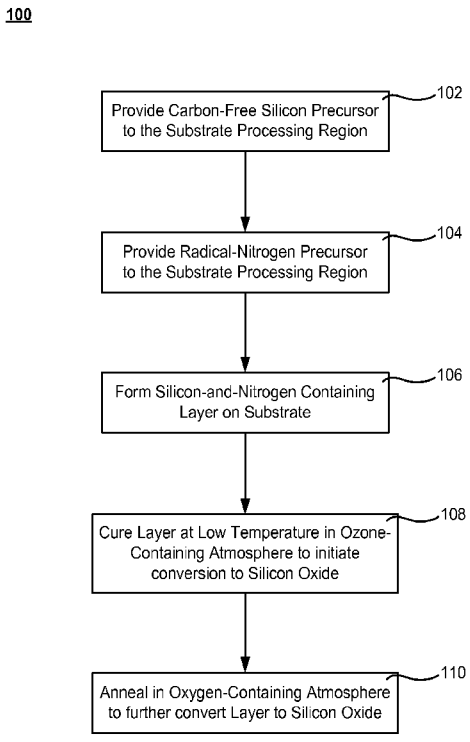


FIG 1

(57) Abstract: A method of forming a silicon oxide layer is described. The method may include the steps of mixing a carbon-free silicon-containing precursor with a radical-nitrogen-and/or-hydrogen precursor, and depositing a silicon-nitrogen-and-hydrogen-containing layer on a substrate. The conversion of the silicon-nitrogen-and-hydrogen-containing layer to a silicon-and- oxygen-containing layer is then initiated by a low temperature anneal (a "cure") in an ozone- containing atmosphere. The conversion of the silicon-and-nitrogen film to silicon oxide in the ozone-containing atmosphere may be incomplete and augmented by a higher temperature anneal in an oxygen-containing environment.

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